

*#17/C  
3/24/03  
VX*

S/N 08/902,133

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes et al.

Examiner: Valencia Wallace

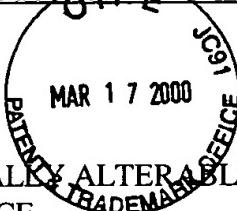
Serial No.: 08/902,133

Group Art Unit: 2815

Filed: July 29, 1997

Docket: 303.356US1

Title: DYNAMIC ELECTRICALLY ALTERABLE PROGRAMMABLE READ ONLY MEMORY DEVICE



PRELIMINARY AMENDMENT

Assistant Commissioner for Patents

Washington, D.C. 20231

When the above-identified patent application is taken up for consideration, please amend the application as follows:

IN THE CLAIMS

Please amend the following claims:

18.(Three times amended) The transistor of claim 28, wherein [the] an area of a capacitor formed by the control electrode, the floating gate, and the intergate dielectric is larger than [the] an area of a capacitor formed by the floating gate, the insulator, and the channel region.

19.(Twice Amended) A transistor comprising:  
a source region;  
a drain region;  
a channel region between the source region and the drain region; [and]  
a floating gate separated from the channel region by an insulator, wherein a barrier energy between the floating gate and the insulator is less than approximately 3.3 eV;  
a control electrode, separated from the floating gate by an intergate dielectric; and  
wherein the intergate dielectric has a permittivity that is higher than a permittivity of silicon dioxide.

29.(Amended) A memory cell comprising:  
a storage electrode [for storing] to store charge;  
a control electrode, separated from a storage electrode by an intergate dielectric; and

03/20/2000 ASAHLE 00000063 08902133

1170.00 0P  
576.00 0P  
01 FC:102  
02 FC:103